NSN 5961-00-025-5886

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-025-5886 **Inclosure Material:** Metal **Overall Length:** Between 0.300 inches and 0.400 inches **Overall Diameter:** 0.424 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Anode **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.424 inches and 0.437 inches **Thread Size:** 0.190 inches **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 2.0 gate trigger voltage, dc and 1.8 on-state voltage, dc **Current Rating Per Characteristic:** 7.00 amperes forward current, total rms nanoamperes and 30.00 milliamperes forward current, total rms preset **Special Features:** Item must comply w/rqmt of desc production standard no. L00876; junction pattern arrangement: pnpn **Thread Series Designator: Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: